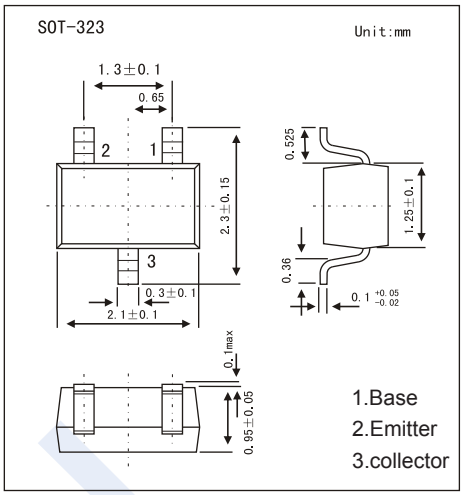
PNP Transistors

BC807W (KC807W)



■ Features

- ● Ldeally suited for automatic insertion
- ● Epitaxial planar die construction
- ● Complementary to BC817W

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-50	V
Collector - Emitter Voltage	V_{CEO}	-45	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	0.2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-45			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -50 V , I_E=0			-0.1	uA
Collector- emittercut-off current	I_{CEO}	V_{CE}= -20 V , I_E=0			-0.2	
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-50mA			-0.7	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C= -500 mA, I_B=- 50mA			-1.2	
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -100mA	100		600	
	$h_{FE(2)}$	V_{CE}=- 1V, I_C= -500mA	40			
Collector output capacitance	C_{ob}	V_{CB}= -10V,f=1MHz			10	pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -10mA,f=100MHz	80			MHz

■ Classification of $h_{fe(1)}$

Type	BC807W-16	BC807W-25	BC807W-40
Range	100-250	160-400	250-600
Marking	5A	5B	5C

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■ Typical Characterisitics